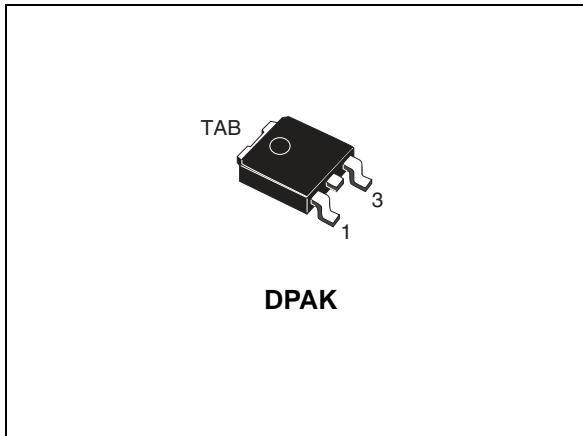


## High voltage fast-switching NPN power transistor

Datasheet - production data



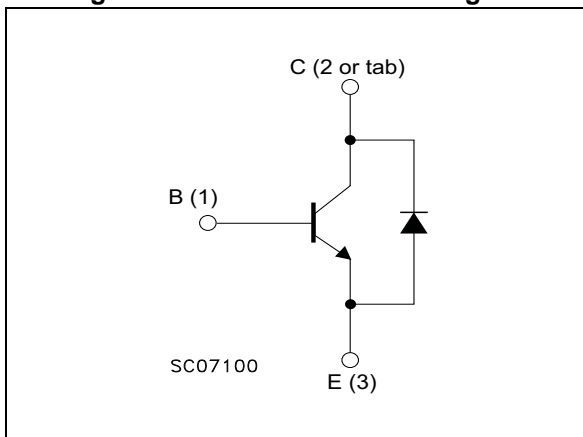
### Features

- NPN transistor
- High voltage capability
- Low spread of dynamic parameters
- Minimum lot-to-lot spread for reliable operation
- Very high switching speed
- Integrated anti-parallel collector - emitter diode

### Applications

- Electronic ballast for fluorescent lighting
- Fly back and forward single transistor low power converters

Figure 1. Internal schematic diagram



### Description

This device is manufactured using high voltage multi epitaxial planar technology for high switching speeds and medium voltage capability. It uses a cellular emitter structure with planar edge termination to enhance switching speeds while maintaining the wide RBSOA. The device is designed for use in lighting applications and low cost switch-mode power supplies.

Table 1. Device summary

Part number	Marking	Package	Packaging
STD127DT4	D127D	DPAK	Tape and reel

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{CES}$	Collector-emitter voltage ( $V_{BE} = 0$ )	700	V
$V_{CEO}$	Collector-emitter voltage ( $I_B = 0$ )	400	V
$V_{EBO}$	Emitter-base voltage ( $I_C = 0$ ; $I_B = 2$ A, $t_p < 10$ $\mu$ s, $T_J = 150$ °C)	$V_{(BR)EBO}$	V
$I_C$	Collector current	4	A
$I_{CM}$	Collector peak current ( $t_p < 5$ ms)	8	A
$I_B$	Base current	2	A
$I_{BM}$	Base peak current ( $t_p < 5$ ms)	4	A
$P_{tot}$	Total dissipation at $T_c \leq 25$ °C	35	W
$T_{stg}$	Storage temperature	-65 to 150	°C
$T_J$	Max. operating junction temperature	150	°C

**Table 3. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thJC}$	Thermal resistance junction-case max	3.57	°C/W
$R_{thJA}$	Thermal resistance junction-ambient max	100	°C/W

## 2 Electrical characteristics

( $T_{\text{case}} = 25^{\circ}\text{C}$  unless otherwise specified)

**Table 4. Electrical characteristics**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{\text{CBO}}$	Collector cut-off current ( $V_{\text{BE}} = 0$ )	$V_{\text{CE}} = 700 \text{ V}$			100	$\mu\text{A}$
$I_{\text{CEO}}$	Collector cut-off current ( $I_{\text{B}} = 0$ )	$V_{\text{CE}} = 400 \text{ V}$			250	$\mu\text{A}$
$V_{(\text{BR})\text{EBO}}$	Emitter - base breakdown voltage ( $I_{\text{C}} = 0$ )	$I_{\text{E}} = 10 \text{ mA}$	9		18	V
$V_{\text{CEO(sus)}}^{(1)}$	Collector-emitter sustaining voltage ( $I_{\text{B}} = 0$ )	$I_{\text{C}} = 100 \text{ mA}$	400			V
$V_{\text{CE(sat)}}^{(1)}$	Collector-emitter saturation voltage	$I_{\text{C}} = 1 \text{ A}$ $I_{\text{B}} = 0.2 \text{ A}$ $I_{\text{C}} = 4 \text{ A}$ $I_{\text{B}} = 1 \text{ A}$			0.3 1.3	V V
$V_{\text{BE(sat)}}^{(1)}$	Base-emitter saturation voltage	$I_{\text{C}} = 1 \text{ A}$ $I_{\text{B}} = 0.2 \text{ A}$			1.2	V
$h_{\text{FE}}^{(1)}$	DC current gain	$I_{\text{C}} = 10 \text{ mA}$ $V_{\text{CE}} = 5 \text{ V}$ $I_{\text{C}} = 1 \text{ A}$ $V_{\text{CE}} = 5 \text{ V}$ $I_{\text{C}} = 4 \text{ A}$ $V_{\text{CE}} = 5 \text{ V}$	7 10 5	25	40	
$V_{\text{F}}$	Diode forward voltage	$I_{\text{F}} = 2 \text{ A}$			2.5	V
$t_{\text{s}}$ $t_{\text{f}}$	Inductive load Storage time Fall time	$I_{\text{C}} = 2 \text{ A}$ $I_{\text{B(on)}} = 0.4 \text{ A}$ $V_{\text{BE(off)}} = -5 \text{ V}$ ; $R_{\text{BB(off)}} = 0$ $V_{\text{CC}} = 200 \text{ V}$ $L = 200 \mu\text{H}$		0.6 0.1		$\mu\text{s}$ ns

1. Pulsed duration = 300  $\mu\text{s}$ , duty cycle  $\leq 1.5\%$ .

## 2.1 Electrical characteristics (curves)

Figure 2. Reverse biased safe operating area

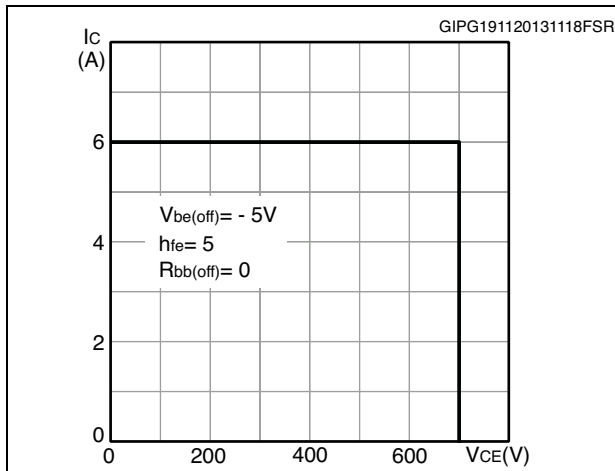


Figure 3. DC current gain

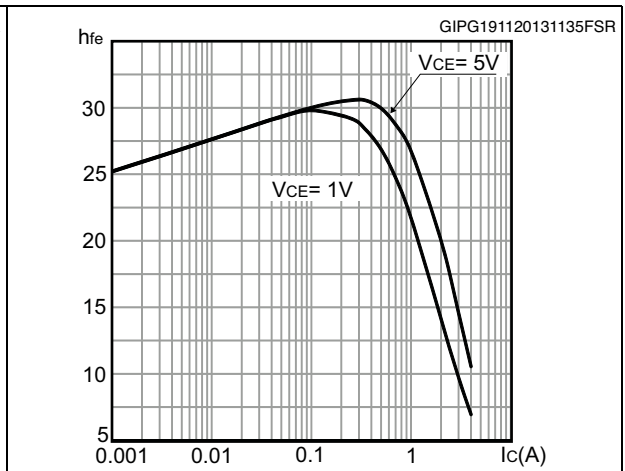


Figure 4. Collector-emitter saturation voltage

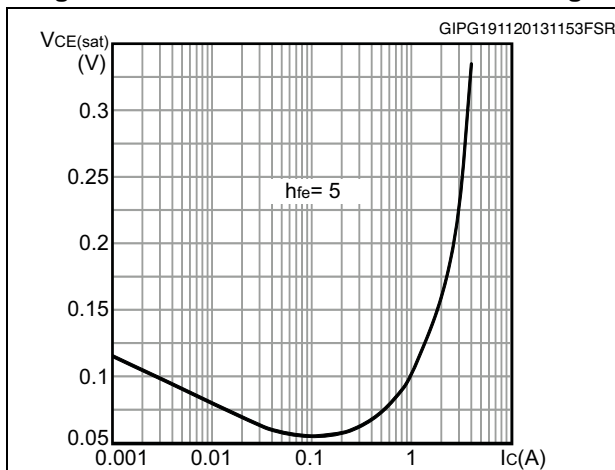


Figure 5. Base-emitter saturation voltage

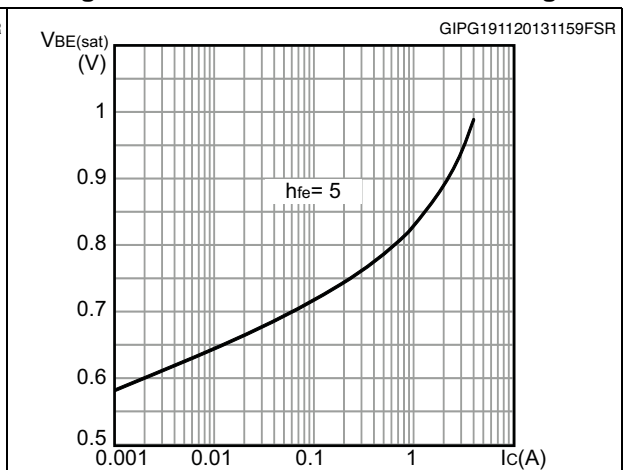


Figure 6. Base-emitter on-voltage

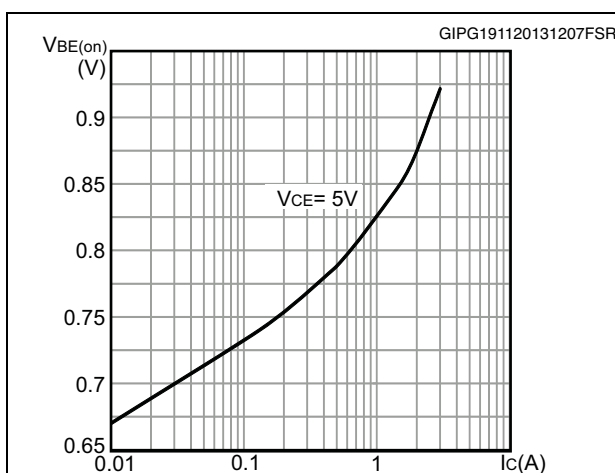


Figure 7. Diode forward voltage vs collector current

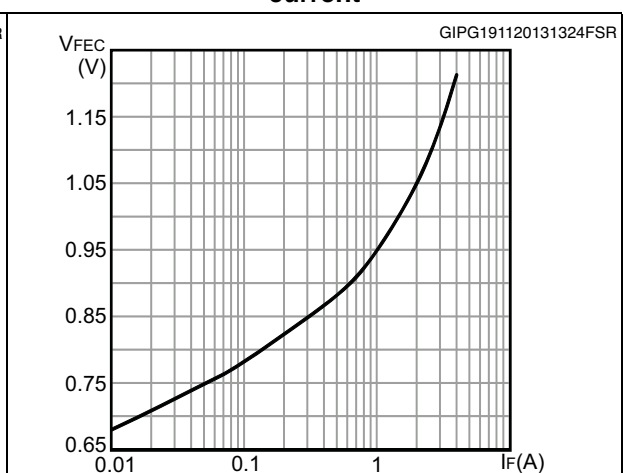


Figure 8. Resistive load switching time

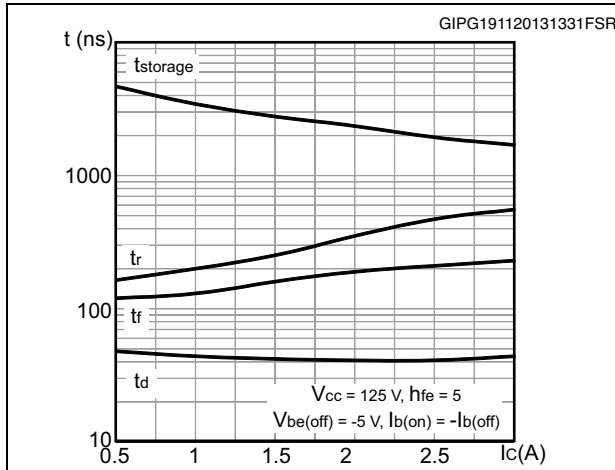
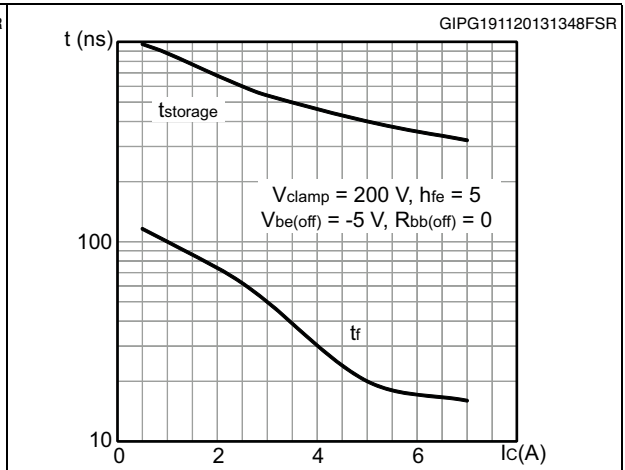
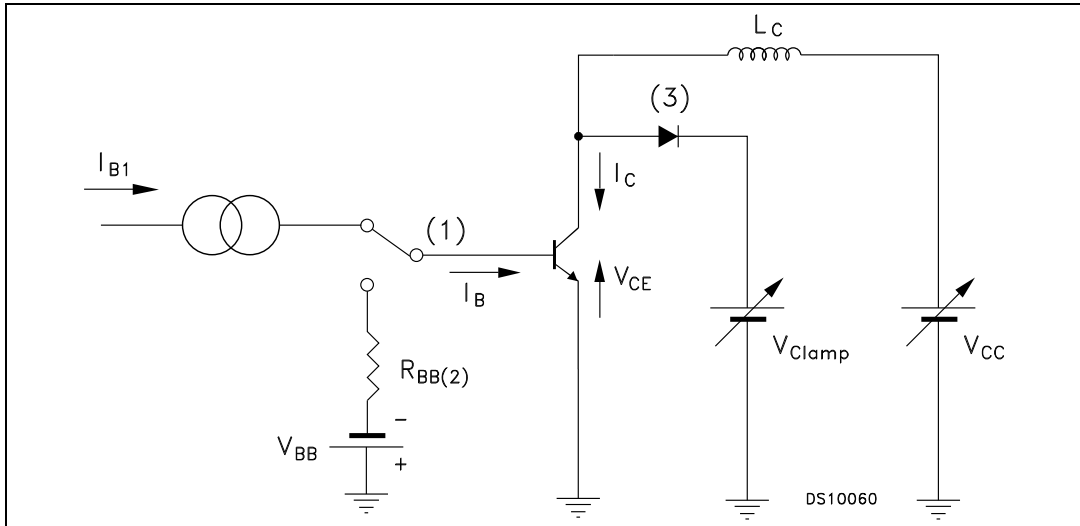


Figure 9. Inductive load switching time



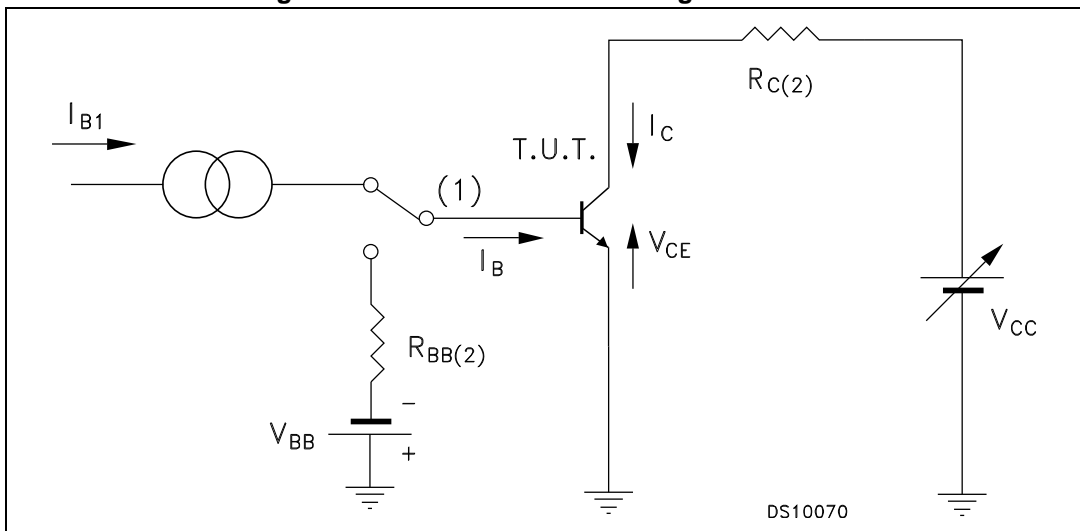
### 3 Test circuits

Figure 10. Inductive load switching test circuit



- 1. Fast electronic switch
- 2. Non-inductive resistor
- 3. Fast recovery rectifier

Figure 11. Resistive load switching test circuit



## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK<sup>®</sup> is an ST trademark.

**Table 5. DPAK (TO-252) type C mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	2.20	2.30	2.38
A1	0.90	1.01	1.10
A2	0.00		0.10
b	0.72		0.85
b4	5.13	5.33	5.46
c	0.47		0.60
c2	0.47		0.60
D	6.00	6.10	6.20
D1	5.25		
E	6.50	6.60	6.70
E1	4.70		
e	2.186	2.286	2.386
H	9.80	10.10	10.40
L	1.40	1.50	1.70
L2	0.90		1.25
L4	0.60	0.80	1.00
θ1	5°	7°	9°
θ2	5°	7°	9°
V2	0°		8°



Figure 12. DPAK (TO-252) type C drawing

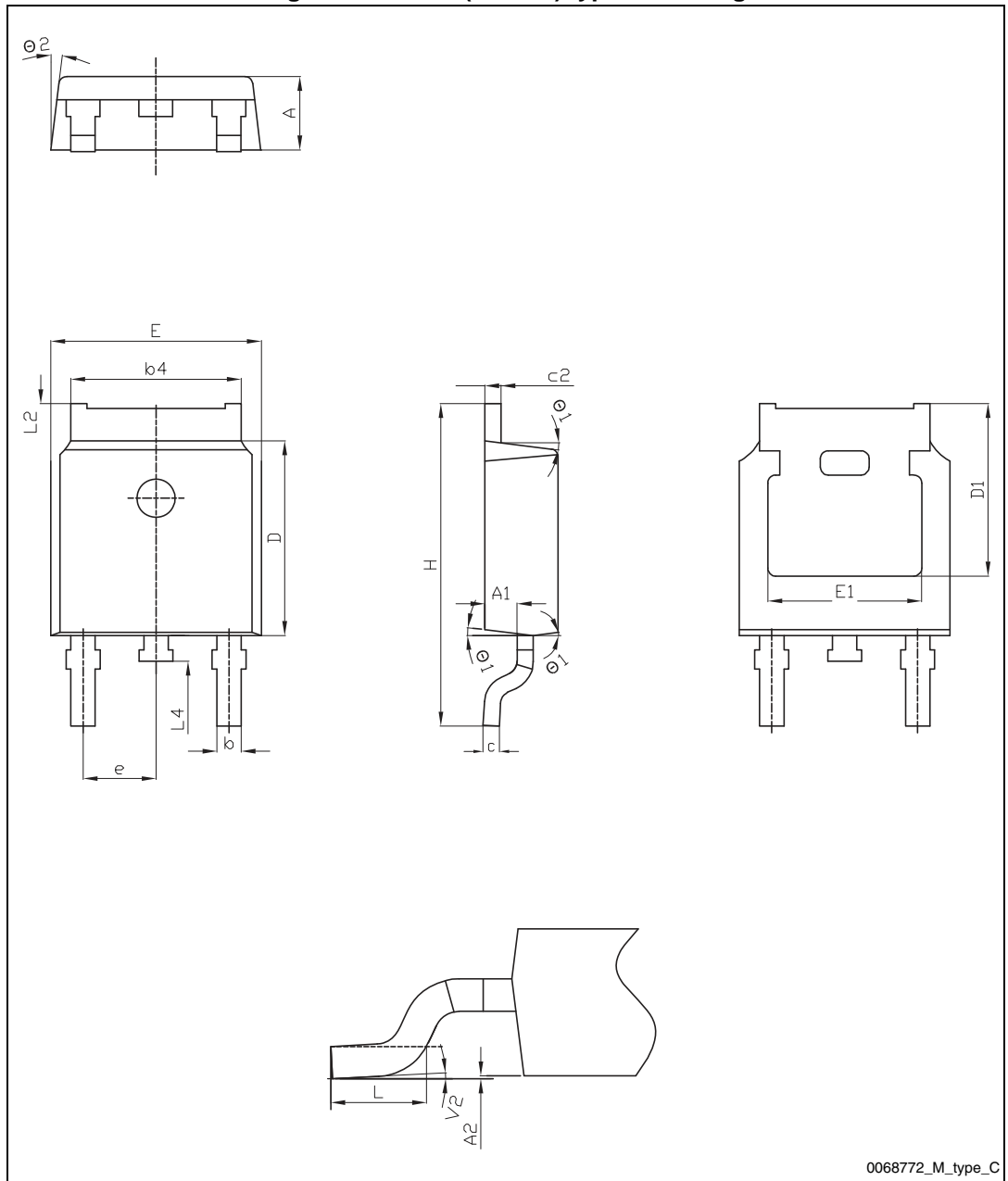
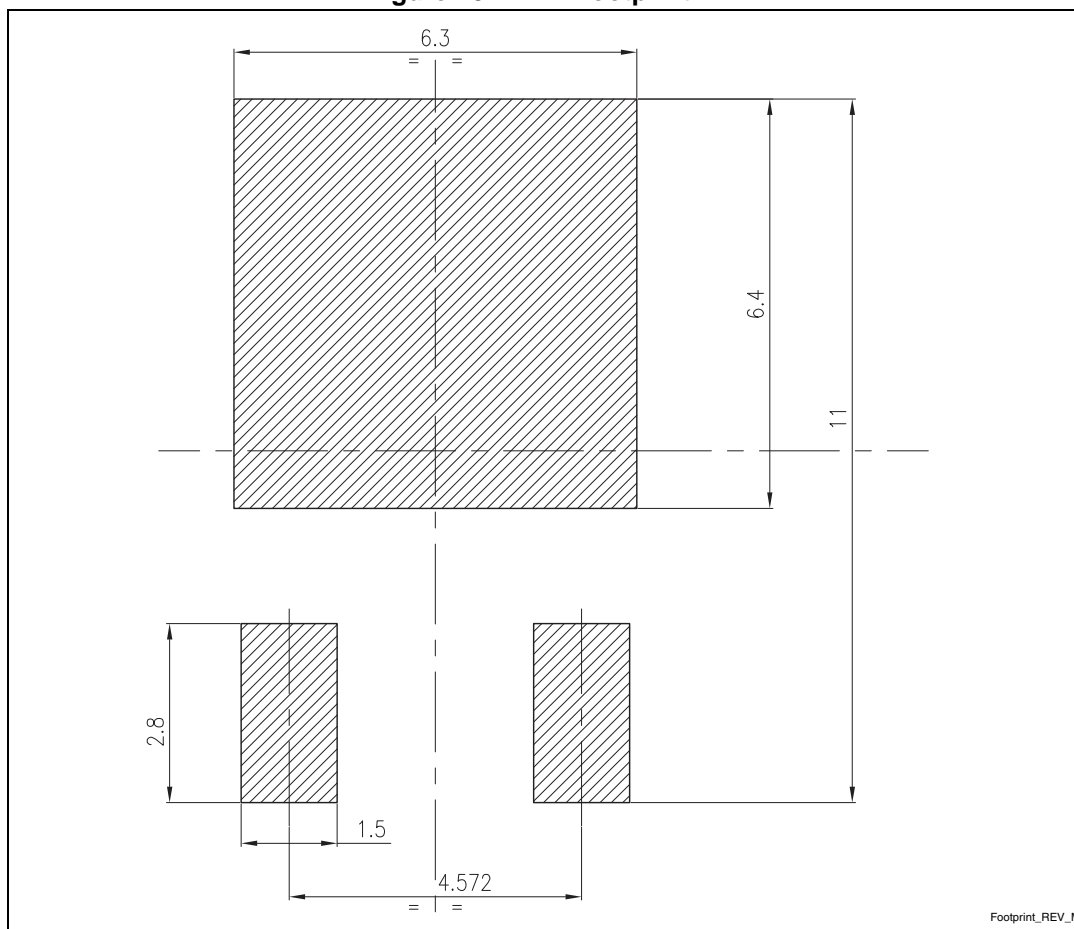


Figure 13. DPAK footprint (a)



a. All dimensions are in millimeters

## 5 Packing mechanical data

Table 6. DPAK (TO-252) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

Figure 14. Tape for DPAK (TO-252)

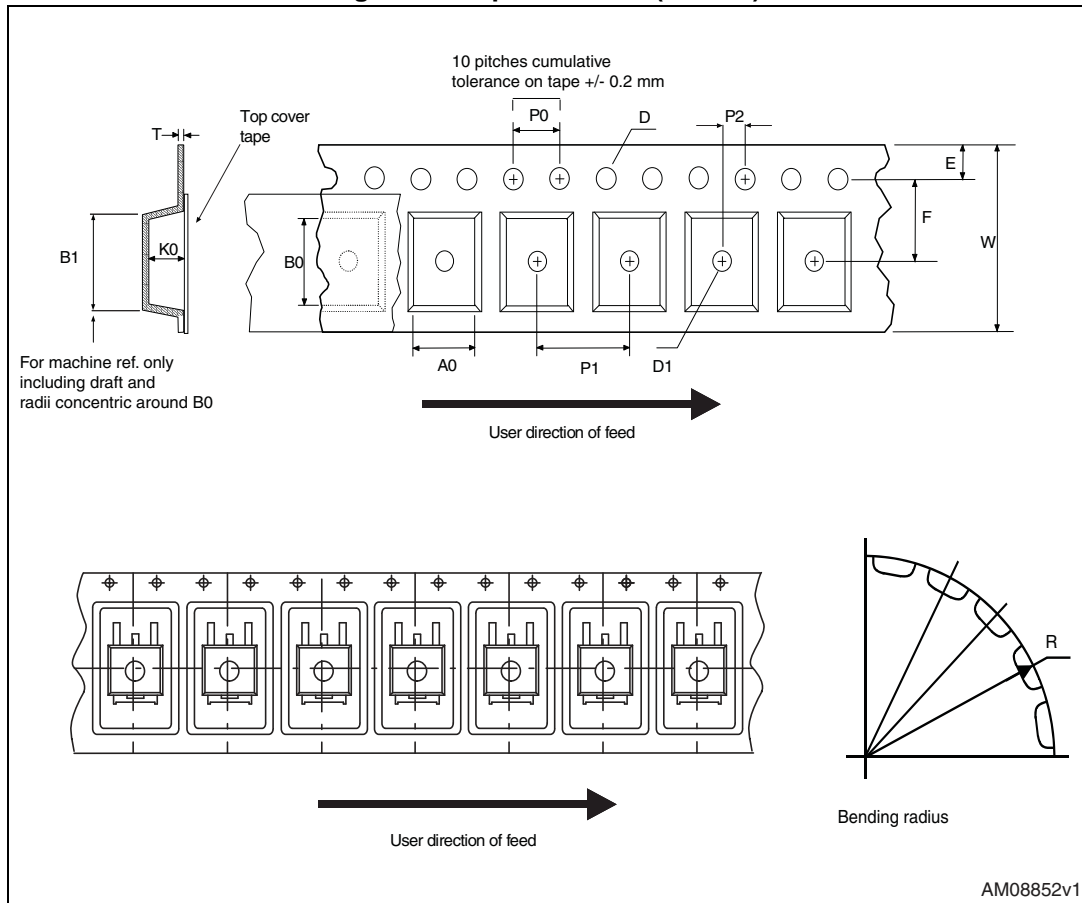
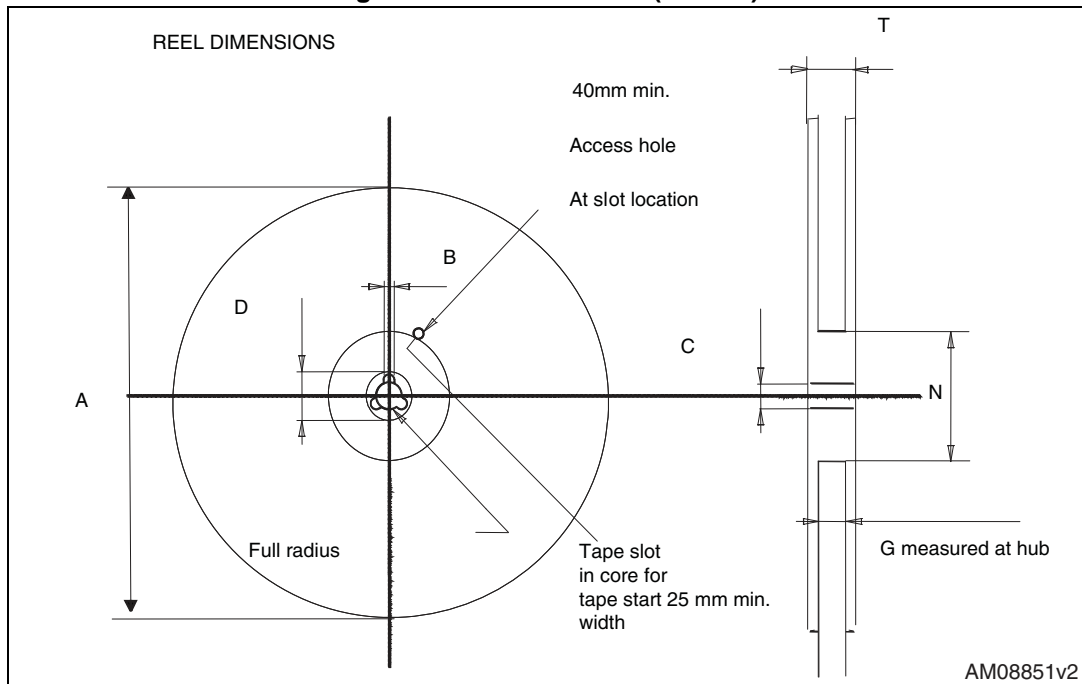


Figure 15. Reel for DPAK (TO-252)



## 6 Revision history

Table 7. Document revision history

Date	Revision	Changes
19-Nov-2013	1	Initial release.

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